# RJH60D5DPQ-A0 

## Features

- Short circuit withstand time (5 $\mu$ s typ.)
- Low collector to emitter saturation voltage
$\mathrm{V}_{\mathrm{CE}(\text { sat })}=1.6 \mathrm{~V}$ typ. (at $\mathrm{I}_{\mathrm{C}}=37 \mathrm{~A}, \mathrm{~V}_{\mathrm{GE}}=15 \mathrm{~V}, \mathrm{Ta}=25^{\circ} \mathrm{C}$ )
- Built in fast recovery diode (100 ns typ.) in one package
- Trench gate and thin wafer technology
- High speed switching
$\mathrm{t}_{\mathrm{f}}=75$ ns typ. (at $\mathrm{V}_{\mathrm{CC}}=300 \mathrm{~V}, \mathrm{~V}_{\mathrm{GE}}=15 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=37 \mathrm{~A}, \mathrm{Rg}=5 \Omega, \mathrm{Ta}=25^{\circ} \mathrm{C}$, inductive load)


## Outline

RENESAS Package code: PRSS0003ZH-A
(Package name: TO-247A)


1. Gate
2. Collector
3. Emitter
4. Collector

## Absolute Maximum Ratings

| Item |  |  | $\left(\mathrm{Ta}=25^{\circ} \mathrm{C}\right)$ |
| :---: | :---: | :---: | :---: |
|  | Symbol | Ratings | Unit |
| Collector to emitter voltage / diode reverse voltage | $\mathrm{V}_{\text {CES }} / \mathrm{V}_{\mathrm{R}}$ | 600 | V |
| Gate to emitter voltage | $\mathrm{V}_{\text {GES }}$ | $\pm 30$ | V |
| Collector current | $\mathrm{I}_{C}$ | 75 | A |
|  | $\mathrm{I}_{C}$ | 37 | A |
| Collector peak current | ic(peak) ${ }^{\text {Note1 }}$ | 150 | A |
| Collector to emitter diode forward current | $\mathrm{I}_{\mathrm{DF}}$ | 30 | A |
| Collector to emitter diode forward peak current | $\mathrm{i}_{\mathrm{DF}}(\text { peak })^{\text {Note1 }}$ | 120 | A |
| Collector dissipation | $\mathrm{P}^{\text {Note2 }}$ | 200 | W |
| Junction to case thermal resistance (IGBT) | $\theta \mathrm{j}-\mathrm{c}^{\text {Note2 }}$ | 0.63 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to case thermal resistance (Diode) | $\theta \mathrm{j}$-cd ${ }^{\text {Note2 }}$ | 2.1 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction temperature | Tj | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature | Tstg | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Notes: 1. $\mathrm{PW} \leq 10 \mu \mathrm{~s}$, duty cycle $\leq 1 \%$
2. Value at $\mathrm{Tc}=25^{\circ} \mathrm{C}$

## Electrical Characteristics

$\left(\mathrm{Ta}=25^{\circ} \mathrm{C}\right)$

| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Zero gate voltage collector current / Diode reverse current | $\mathrm{I}_{\text {CES }} / \mathrm{I}_{\mathrm{R}}$ | - | - | 5 | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{CE}}=600 \mathrm{~V}, \mathrm{~V}_{\mathrm{GE}}=0$ |
| Gate to emitter leak current | Iges | - | - | $\pm 1$ | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{GE}}= \pm 30 \mathrm{~V}, \mathrm{~V}_{\text {CE }}=0$ |
| Gate to emitter cutoff voltage | $\mathrm{V}_{\text {GE(off) }}$ | 4.0 | - | 6.0 | V | $\mathrm{V}_{\text {CE }}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=1 \mathrm{~mA}$ |
| Collector to emitter saturation voltage | $\mathrm{V}_{\mathrm{CE} \text { (sat) }}$ | - | 1.6 | 2.2 | V | $\mathrm{I}_{\mathrm{C}}=37 \mathrm{~A}, \mathrm{~V}_{\mathrm{GE}}=15 \mathrm{~V}^{\text {Note3 }}$ |
|  | $\mathrm{V}_{\mathrm{CE} \text { (sat) }}$ | - | 2.0 | - | V | $\mathrm{I}_{\mathrm{C}}=75 \mathrm{~A}, \mathrm{~V}_{\mathrm{GE}}=15 \mathrm{~V}^{\text {Note3 }}$ |
| Input capacitance | Cies | - | 1900 | - | pF | $\begin{aligned} & \mathrm{V}_{\mathrm{CE}}=25 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{GE}}=0 \\ & \mathrm{f}=1 \mathrm{MHz} \end{aligned}$ |
| Output capacitance | Coes | - | 120 | - | pF |  |
| Reveres transfer capacitance | Cres | - | 60 | - | pF |  |
| Total gate charge | Qg | - | 78 | - | nC | $\begin{aligned} & \mathrm{V}_{\mathrm{GE}}=15 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{CE}}=300 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{C}}=37 \mathrm{~A} \end{aligned}$ |
| Gate to emitter charge | Qge | - | 12 | - | nC |  |
| Gate to collector charge | Qgc | - | 36 | - | nC |  |
| Switching time | $\mathrm{t}_{\mathrm{d}(\mathrm{on})}$ | - | 50 | - | ns | $\begin{aligned} & \mathrm{V}_{\mathrm{CC}}=300 \mathrm{~V}, \mathrm{~V}_{\mathrm{GE}}=15 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{C}}=37 \mathrm{~A} \\ & \mathrm{Rg}=5 \Omega \\ & \text { Inductive load } \end{aligned}$ |
|  | $\mathrm{t}_{\mathrm{r}}$ | - | 35 | - | ns |  |
|  | $\mathrm{t}_{\mathrm{d}(\mathrm{fff})}$ | - | 130 | - | ns |  |
|  | $\mathrm{t}_{\mathrm{f}}$ | - | 50 | - | ns |  |
| Short circuit withstand time | $\mathrm{t}_{\mathrm{sc}}$ | 3.0 | 5.0 | - | $\mu \mathrm{s}$ | $\mathrm{V}_{\mathrm{CC}} \leq 360 \mathrm{~V}, \mathrm{~V}_{\mathrm{GE}}=15 \mathrm{~V}$ |


| FRD Forward voltage | $\mathrm{V}_{\mathrm{F}}$ | - | 1.4 | 1.9 | V | $\mathrm{I}_{\mathrm{F}}=30 \mathrm{~A}$ Note3 |
| :--- | :---: | :---: | :---: | :---: | :---: | :--- |
| FRD reverse recovery time | $\mathrm{t}_{\mathrm{rr}}$ | - | 100 | - | ns | $\mathrm{I}_{\mathrm{F}}=30 \mathrm{~A}$ <br> $\mathrm{di}_{\mathrm{F}} / \mathrm{dt}=100 \mathrm{~A} / \mu \mathrm{s}$ |

Notes: 3. Pulse test.

## Main Characteristics



Collector to Emitter Satularion Voltage vs. Gate to Emitter Voltage (Typical)


Transfer Characteristics (Typical)


Collector to Emitter Satularion Voltage vs. Gate to Emitter Voltage (Typical)


Diode Forward Characteristics (Typical)




## Package Dimension



## Ordering Information

| Orderable Part Number | Quantity | Shipping Container |
| :---: | :--- | :--- |
| RJH60D5DPQ-A0-T0 | 240 pcs | Box (Tube) |

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